



CS-01-111

January 5, 2004

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/676,896 10/01/03 |
Vincent Ho et al.
PROCESS TO MANUFACTURE NONVOLATILE
MOS MEMORY DEVICE
| _____ |

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

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P.O. Box 1450, Alexandria, VA 22313-1450, on January 07, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 1/27/04

"A Silicon Nanocrystals Based Memory," Tiwari et al., Appl. Phys. Lett. 68(10), March 4, 1996, pp. 1377-1379, demonstrates quasi-nonvolatile MOS memory devices employing silicon nanocrystal charge-storage sites produced by ion implantation into the gate oxide.

Ya-Chin King et al., "MOS Memory Using Germanium Nanocrystals Formed by Thermal Oxidation of Si_{1-x}Ge_x," IEDM Tech. Digest, 1998, pp. 115-118, discloses a novel technique of fabricating germanium nanocrystal quasi-nonvolatile memory device.

CS-01-074, Serial No. 10/087,506, Filed March 1, 2002, now issued as U.S. Patent 6,656,792, "Nanocrystal Flash Memory Device and Manufacturing Method Therefor," assigned to a common assignee, discusses using radio-frequency co-sputtering and rapid thermal annealing to form the oxide layer containing germanium nanocrystals.

U.S. Patent 6,128,243 to Chan et al., "Shadow Memory for a SRAM and Method," discloses a memory for a SRAM using germanium Nanocrystals.

U.S. Patent 5,783,498 to Dotta, "Method of Forming Silicon Dioxide Film Containing Germanium Nanocrystals," discloses a process to form germanium Nanocrystals.

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U.S. Patent 6,060,743 to Sugiyama et al., "Semiconductor Memory Device Having Multilayer Group IV Nanocrystal Quantum Dot Floating Gate and Method of Manufacturing the Same," discloses a memory device using germanium Nanocrystals.

U.S. Patent 6,090,666 to Ueda et al., "Method for Fabricating Semiconductor Nanocrystal and Semiconductor Memory Device Using the Semiconductor Nanocrystal," discloses a memory device using germanium Nanocrystals.

Sincerely,

A handwritten signature in black ink, appearing to read 'S. B. Ackerman', with a long horizontal flourish extending to the right.

Stephen B. Ackerman,
Reg. No. 37761

Form PTO-1449

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

(Use several sheets if necessary)

Document Number (Sequence)

CS-01-111

Application Number

10/676,896

Applicant

Vincent Ho et al.

Filing Date

10/01/03

Drawn Art Unit

U. S. PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	NUMO DATE X APPROPRIATE
6128243	10/3/00	Chen et al.	365	227	12/3/99
5783498	7/2/98	Dotta	438	778	5/28/96
6060743	5/9/00	Sugiyama et al.	257	321	5/20/98
6090666	7/18/00	Ueda et al.	438	257	9/30/98
6656792	12/2/03	Choi et al.	438	257	3/1/02

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation
					YES NO

OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)

-	Ya-Chin King et al., "MOS Memory Using Germanium Nanocrystals Formed by Thermal Oxidation of Si _{1-x} Ge _x ", IEDM Tech. Digest, 1998, pp. 115-118.
-	"A Silicon Nanocrystals Based Memory", Tiwari et al., Appl. Phys. Lett. 68(10), pp. 1377-1379, March 4, 1996.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.